

IN THE CLAIMS

1. (Currently Amended) A method for reconstructing an integrated circuit package comprising:

deconstructing an integrated circuit package for exposing a wire bond pad and a lead frame located therein;

attaching a die to the exposed wire bond pads pad of a the lead frame so that the second die is electrically connected to the lead frame; ~~and~~

encapsulating the die and the wire bond pads in an encapsulant; and

reshaping an upper surface of the encapsulant where at least a portion of the encapsulant reshaping is performed by a lapping process.

2. (Original) A method according to claim 1, wherein lapping is performed by an abrasive or ablative lapping process.

3. (Original) A method according to claim 1, wherein lapping is performed by a mechanical, chemical, or electromagnetic lapping process.

4. (Original) A method according to claim 1, wherein encapsulating the die and the wire bond pads results in the encapsulant having a convex or concave an upper surface, and reshaping the encapsulant results in the encapsulant having a planar an upper surface.

5. (Original) A method according to claim 1, further comprising marking the reshaped upper surface of the encapsulant.

6. (Original) A method according to claim 1, wherein the reshaped upper surface of the encapsulant is sufficiently flat to permit labeling by printing, photolithographic or mechanical marking techniques to simulate a production transfer molded encapsulated IC package, the method further comprising marking the reshaped upper surface of the encapsulant.

7. (Original) A method according to claim 1, wherein lapping is performed using a laser or another source of electromagnetic radiation.

8. (Original) A method according to claim 1, wherein lapping is performed using a planar abrasive surface.
9. (Original) A method according to claim 1, wherein lapping is performed using a planar abrasive surface attached to a wheel or belt.
10. (Original) A method according to claim 1, wherein lapping is performed using a planar abrasive surface sufficiently large to permit more than one package to be lapped at the same time.
11. (Original) A method according to claim 1, wherein lapping is performed by chemical etching.
12. (Original) A method according to claim 1, wherein lapping is performed using a gas-jet or liquid-jet containing a particular material.
13. (Original) A method according to claim 1, wherein lapping is performed via a mechanical grind.
14. (Original) A method according to claim 1, wherein lapping is performed using a combination of mechanical and chemical ablation.
15. (Original) A method according to claim 1, wherein lapping is performed using a combination of mechanical and electromagnetic ablation.
16. (Original) A method according to claim 1, wherein lapping is performed using laser ablation.
17. (Original) A method according to claim 1, wherein lapping is performed using a combination of electromagnetic and chemical ablation.

18. (Original) A method according to claim 1, wherein lapping is performed by impinging an ultra-fine particulate using a high pressure gas-jet against the material to be lapped.
19. (Original) A method according to claim 1, wherein lapping is performed by impinging an ultra-fine particulate under high pressure against the material to be lapped.
20. (Original) A method according to claim 1, wherein lapping is performed by delivering a pulsating liquid-jet under high pressure against the material to be lapped.
21. (Original) A method according to claim 1, wherein lapping is performed by plasma etching.
22. (Original) A method according to claim 1, wherein lapping is performed by a pressurized liquid against the material to be lapped.